General Description

The AGM028N08A combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
85V	2.8mΩ	170A

PDFN5*6 Pin Configuration

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM028N08A	AGM028N08A	PDFN5*6	----	----	3000

Table 1. Absolute Maximum Ratings (TA=25℃)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	85	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25℃) **(Note 1)**	170	A
	Drain Current-Continuous(Tc=100℃)	108	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed **(Note 2)**	680	A
PD	Maximum Power Dissipation(Tc=25℃)	167	w
	Maximum Power Dissipation(Tc=100℃)	67	w
EAS	Avalanche energy **(Note 3)**	530	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State)[1]	---	50	℃/W
RθJC	Thermal Resistance Junction-Case[1]	---	0.75	℃/W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	85	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=68V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	2.0	3.0	4.0	V
gFS	Forward Transconductance	VDS=10V,ID=15A	--	10	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=15A	--	2.8	3.5	mΩ
		VGS=4.5V, ID=20A	--	--	--	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=50V,VGS=0V, F=1MHZ	--	3100	--	pF
Coss	Output Capacitance		--	1240	--	pF
Crss	Reverse Transfer Capacitance		--	63	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	1.55	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=50V, ID=30A,RGEN=3Ω	--	13.2	--	nS
tr	Turn-on Rise Time		--	17.8	--	nS
td(off)	Turn-Off Delay Time		--	55.2	--	nS
tf	Turn-Off Fall Time		--	27.9	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=50V, ID=30A	--	59.5	--	nC
Qgs	Gate-Source Charge		--	13.5	--	nC
Qgd	Gate-Drain Charge		--	19.8	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	170	A
VSD	Forward on Voltage	VGS=0V,IS=20A	--	--	1.0	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs , TJ=25℃	--	56	--	ns
Qrr	Reverse Recovery Charge		--	79	--	nc

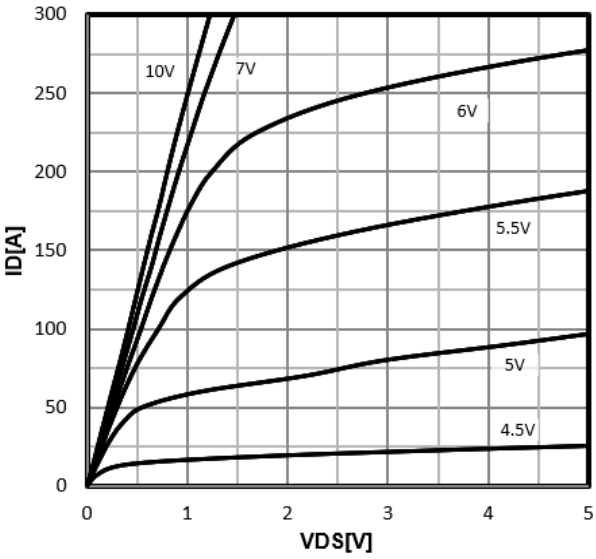
Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25℃

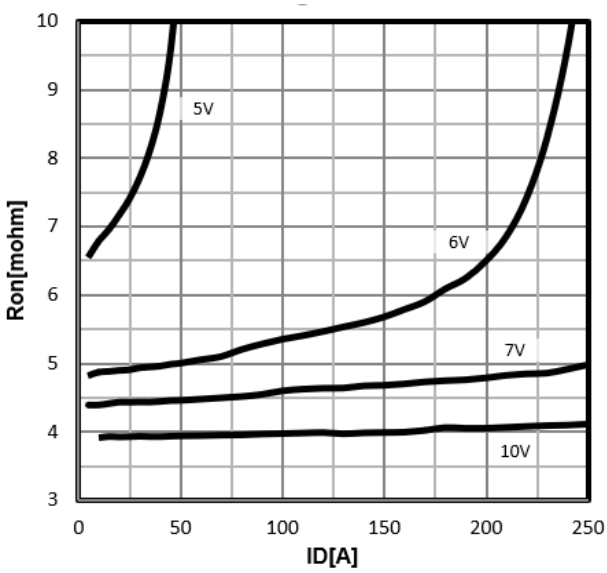
Typ. output characteristics

$I_D=f(V_{DS})$



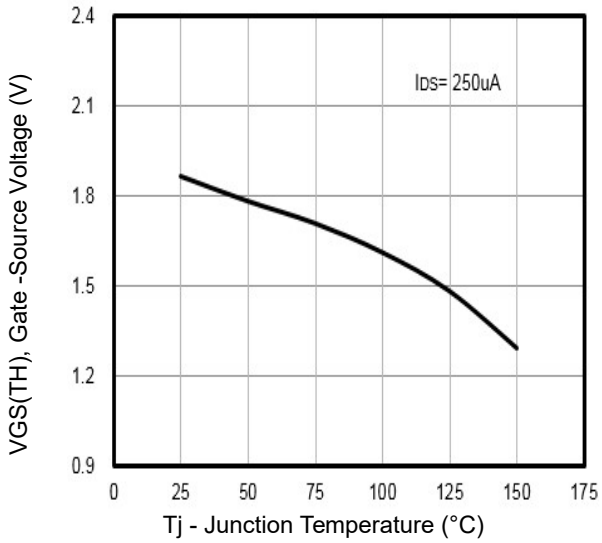
Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$



Typ. transfer characteristics

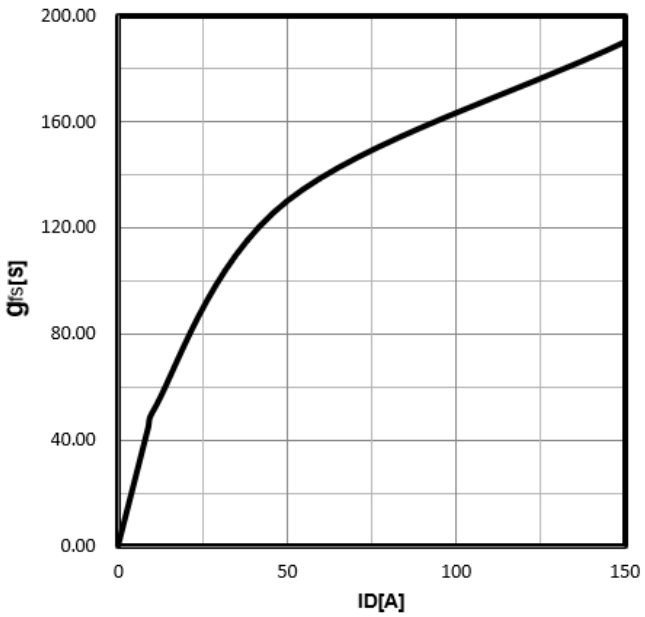
$I_D=f(V_{GS})$



$V_{GS(TH)}$ Gate -Source Voltage Vs. Tj

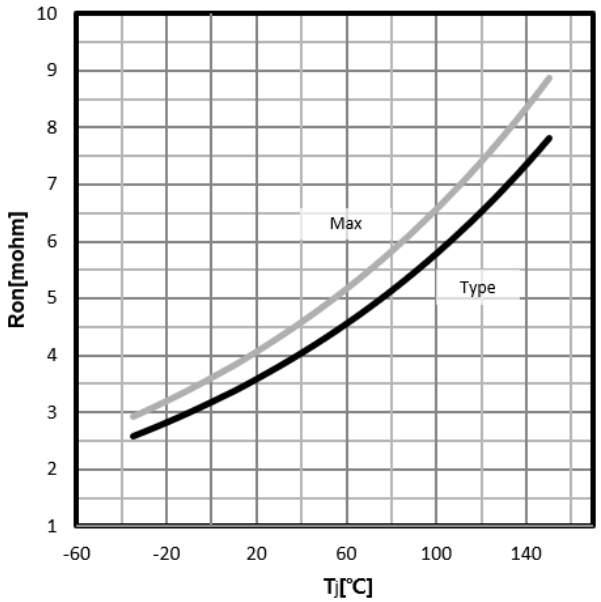
Typ. forward transconductance

$g_{fs}=f(I_D)$



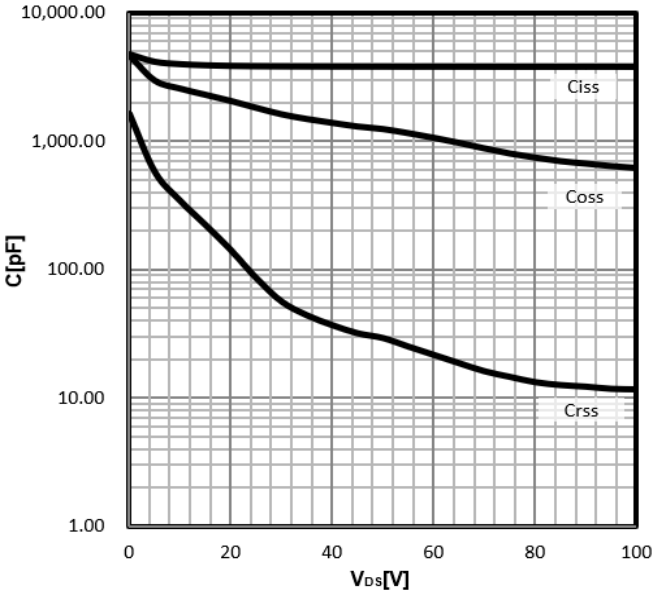
Drain-source on-state resistance

$R_{DS(on)}=f(T_j)$; I_D=56A; V_{GS}=10V



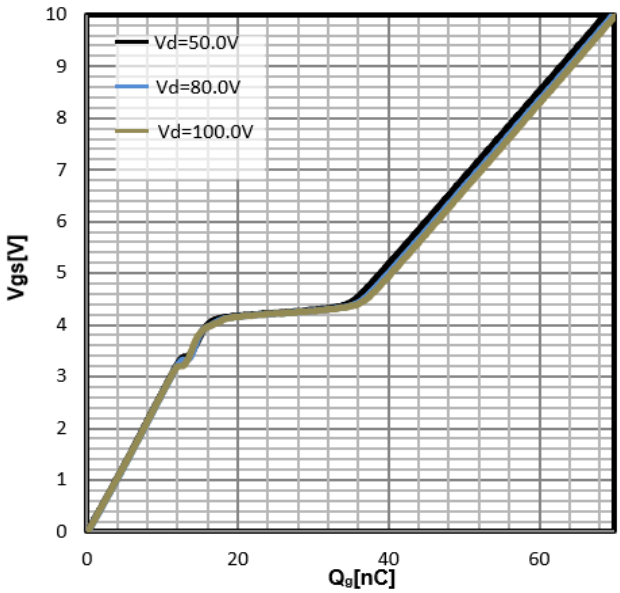
Typ. capacitances

C =f(V_{DS}); V_{GS}=0V; f =1MHz



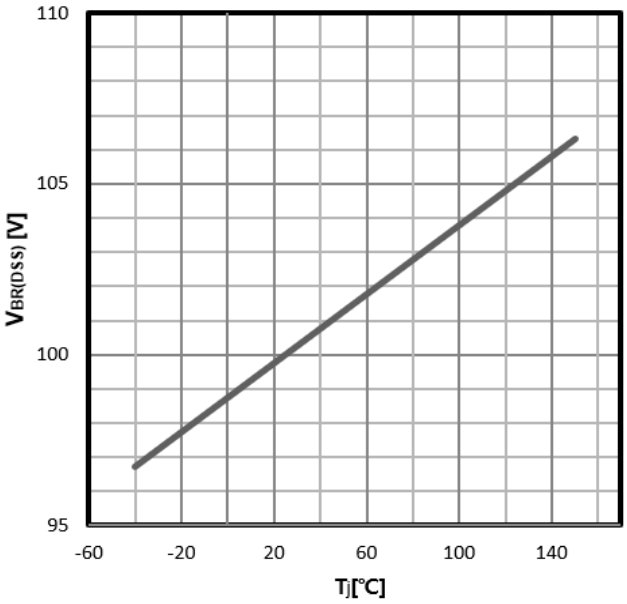
Typ. gate charge

$V_{GS}=f(Q_{gate})$; I_D=20A



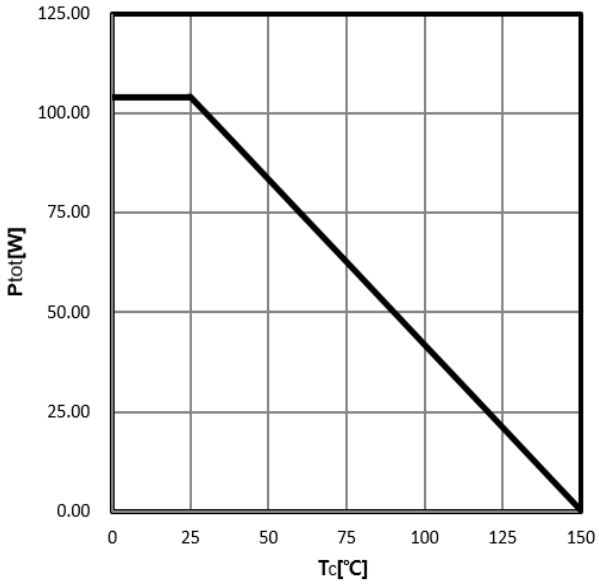
Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j)$; I_D=250uA



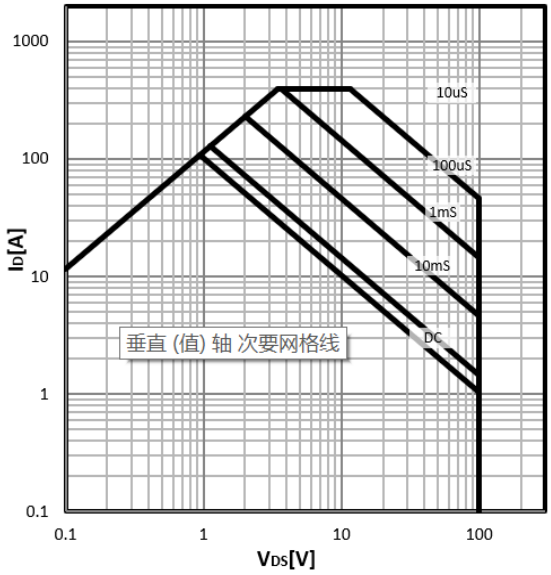
Power Dissipation

$P_{tot}=f(T_C)$



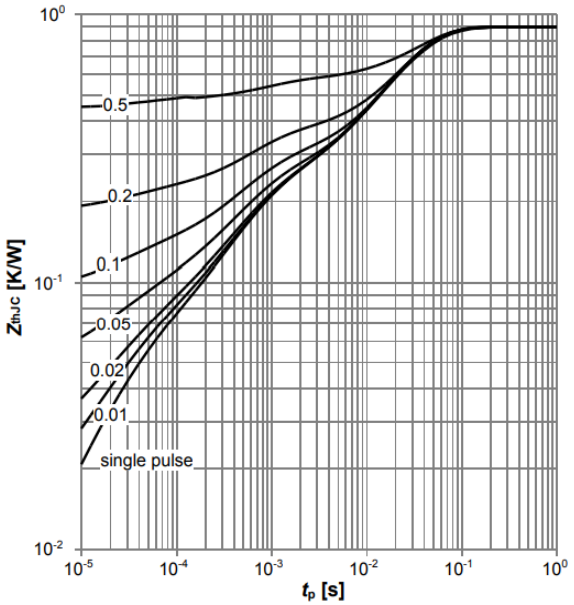
Safe operating area

$I_D=f(V_{DS})$

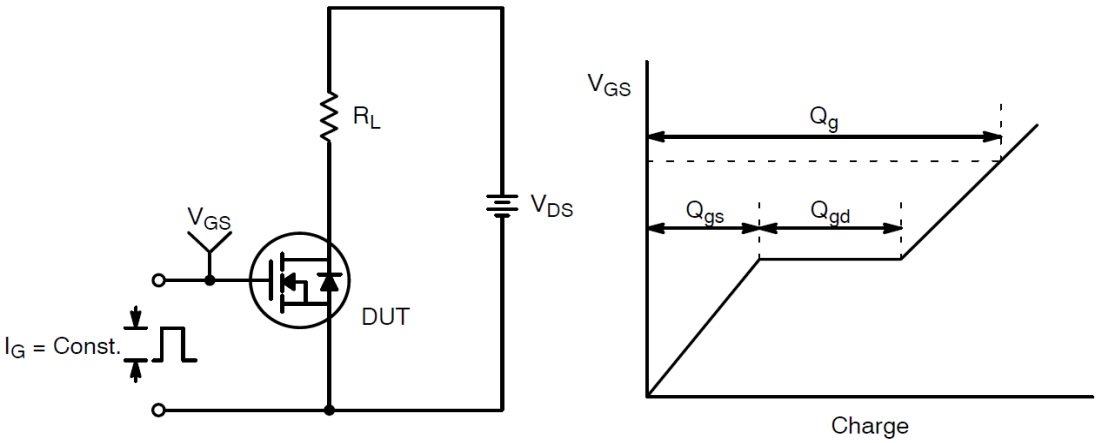


Max. transient thermal impedance

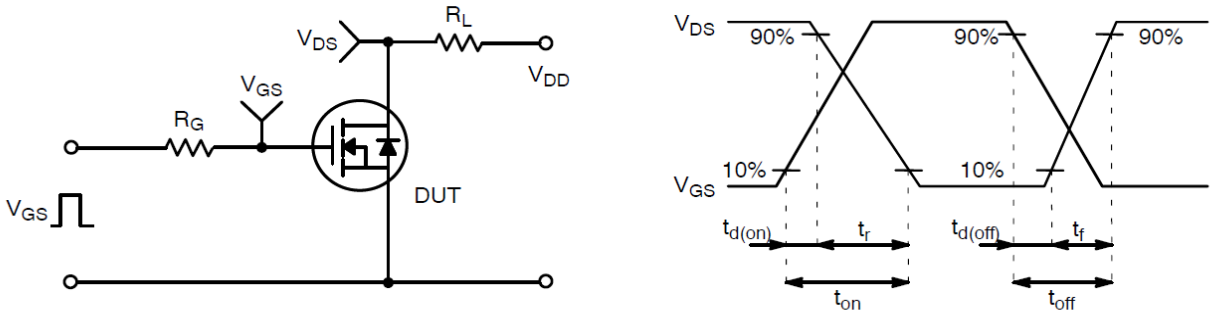
$Z_{thJC}=f(t_p)$



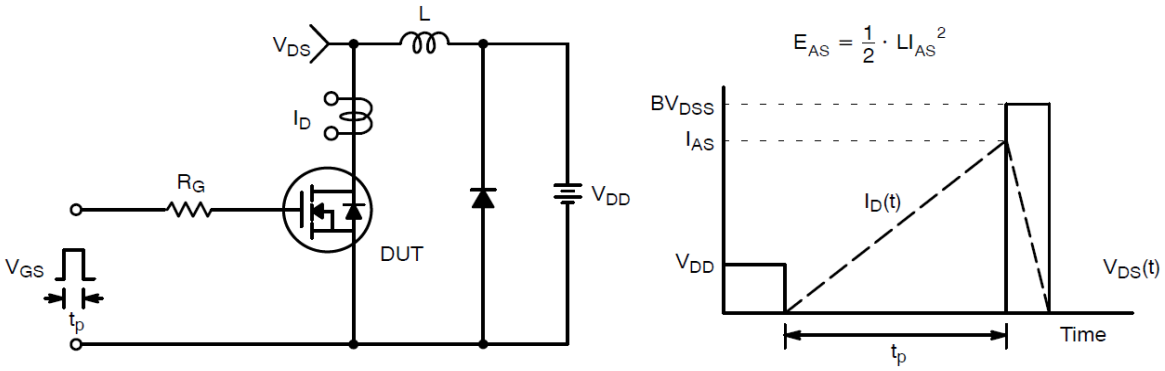
Test Circuit and Waveform:



Gate Charge Test Circuit & Waveform

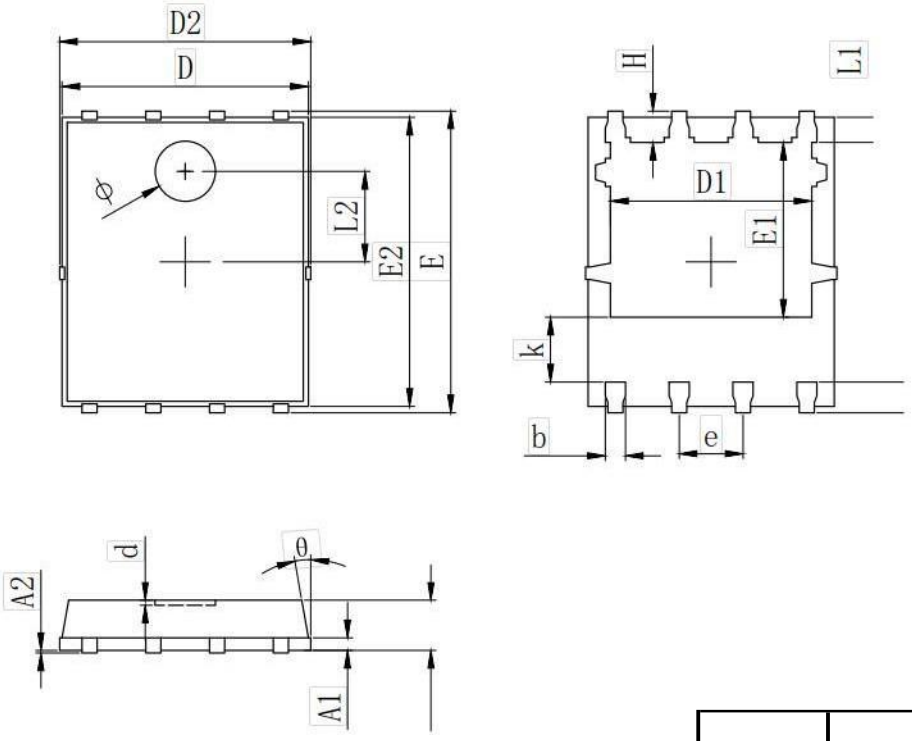


Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

●Dimensions（DFN5×6）



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0~0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
∅	1.100	1.200	1.300
d			0.100

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